



IRF1010NL Information



For Reference Only

Part Number IRF1010NL

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 55V 85A TO-262

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF1010NL Specifications

Manufacturer Part Number IRF1010NL Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 85A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 120nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3210pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 180W (Tc) Rds On (Max) @ Id, Vgs 11 mOhm @ 43A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA Report errors?		
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SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C85A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs120nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3210pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)180W (Tc)Rds On (Max) @ Id, Vgs11 mOhm @ 43A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 85A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 120nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3210pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 43A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case N-Channel N-Chanle N	Package	TO-262-3 Long Leads, I2Pak, TO-262AA
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C B5A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs In mOhm @ 43A, 10V Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) MOSFET (Metal Oxide) MOSFET (Metal Oxide) MOSFET (Metal Oxide) 85A (Tc)	Series	HEXFET?
Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C85A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs120nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3210pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)180W (Tc)Rds On (Max) @ Id, Vgs11 mOhm @ 43A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 120nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 43A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case 85A (Tc) 10V 4V @ 250μA 3210pF @ 25V 520V FET Feature -5°C TO-262-3 Long Leads, 12Pak, TO-262AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs120nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3210pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)180W (Tc)Rds On (Max) @ Id, Vgs11 mOhm @ 43A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Drain to Source Voltage (Vdss)	55V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs In mOhm @ 43A, 10V Operating Temperature Supplier Device Package Package / Case AV @ 250μA 120nC @ 10V 3210pF @ 25V 420V FET Feature - - Through Hole Through Hole TO-262-3 Long Leads, I2Pak, TO-262AA	Current - Continuous Drain (Id) @ 25°C	85A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 43A, 10V Operating Temperature Operating Type Through Hole Supplier Device Package Package / Case 120nC @ 10V 3210pF @ 25V 120nC 180W (Tc) 180W (Tc) 180W (Tc) 180W (Tc) 11 mOhm @ 43A, 10V -55°C ~ 175°C (TJ) Through Hole	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 43A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)180W (Tc)Rds On (Max) @ Id, Vgs11 mOhm @ 43A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	Gate Charge (Qg) (Max) @ Vgs	120nC @ 10V
FET Feature - 180W (Tc) Rds On (Max) @ Id, Vgs	Input Capacitance (Ciss) (Max) @ Vds	3210pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 43A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs11 mOhm @ 43A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Power Dissipation (Max)	180W (Tc)
Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Rds On (Max) @ Id, Vgs	11 mOhm @ 43A, 10V
Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Mounting Type	Through Hole
	Supplier Device Package	TO-262
Report errors?	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
		Report errors?

IRF1010NL Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF1010NL Payment Methods



















IRF1010NL Shipping Methods













If you have any question about IRF1010NL, please do not hesitate to contact us!

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